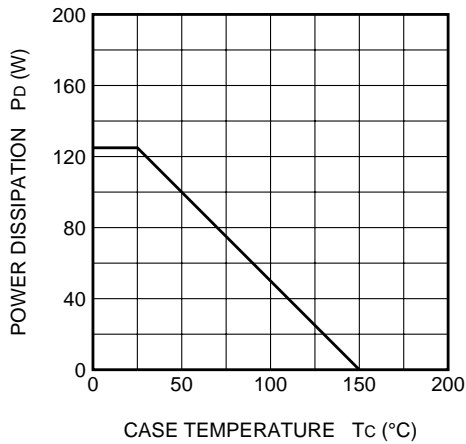


ELECTRICAL CHARACTERISTICS (Tch = 25°C)

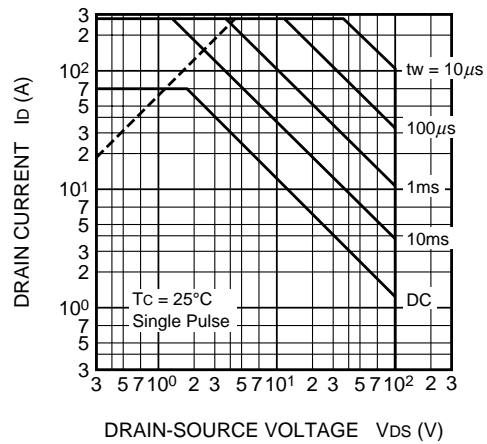
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	100	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 100V, VGS = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS (ON)	Drain-source on-state resistance	ID = 35A, VGS = 10V	—	13	17	mΩ
rDS (ON)	Drain-source on-state resistance	ID = 35A, VGS = 4V	—	14	18	mΩ
VDS (ON)	Drain-source on-state voltage	ID = 35A, VGS = 10V	—	0.46	0.60	V
yfs	Forward transfer admittance	ID = 35A, VDS = 10V	—	68	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	8200	—	pF
Coss	Output capacitance		—	1150	—	pF
Crss	Reverse transfer capacitance		—	600	—	pF
td (on)	Turn-on delay time	VDD = 50V, ID = 35A, VGS = 10V, RGEN = RGS = 50Ω	—	54	—	ns
tr	Rise time		—	140	—	ns
td (off)	Turn-off delay time		—	830	—	ns
tf	Fall time		—	350	—	ns
VSD	Source-drain voltage	IS = 35A, VGS = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	1.00	°C/W
trr	Reverse recovery time	IS = 70A, dis/dt = -100A/μs	—	115	—	ns

PERFORMANCE CURVES

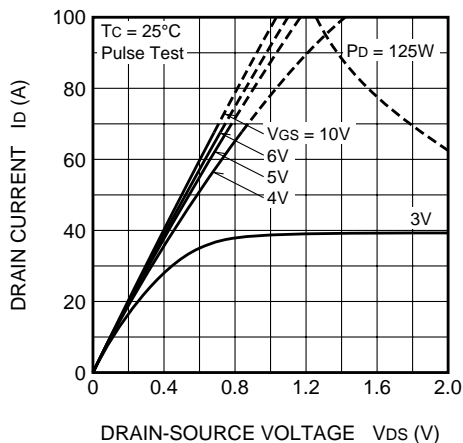
POWER DISSIPATION DERATING CURVE



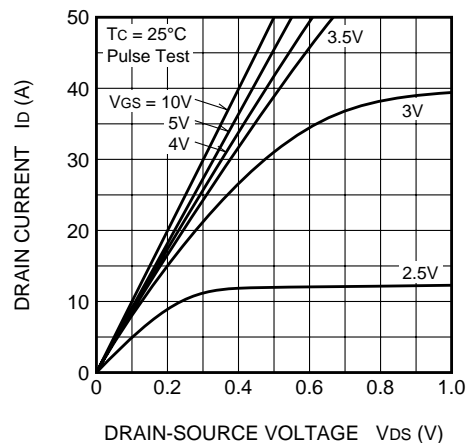
MAXIMUM SAFE OPERATING AREA

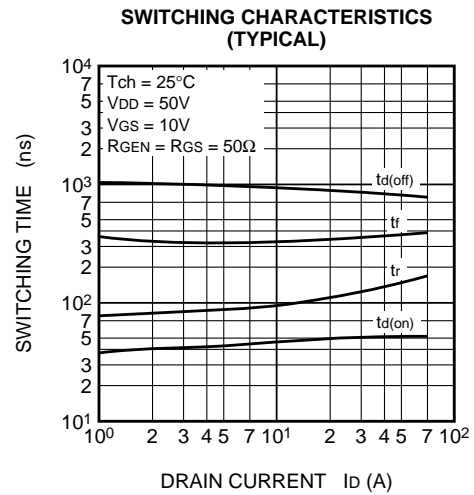
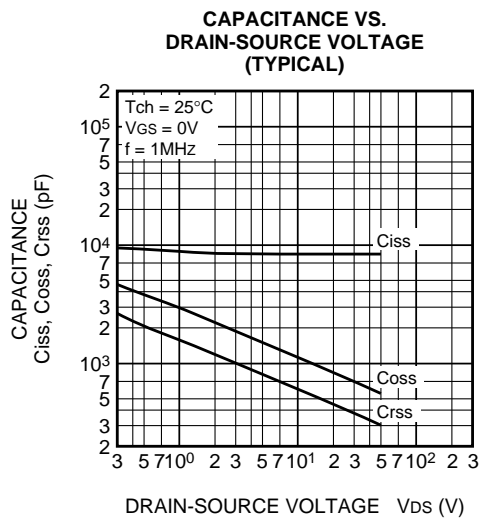
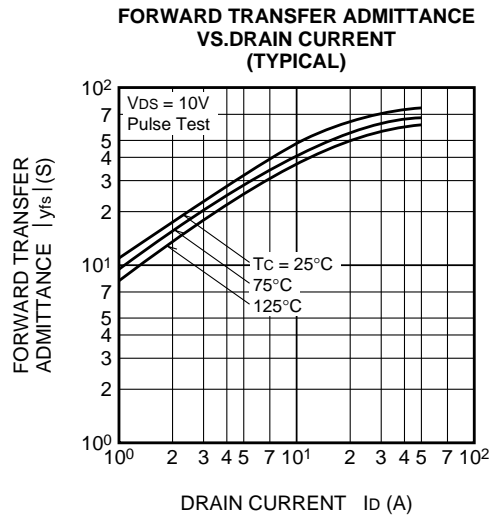
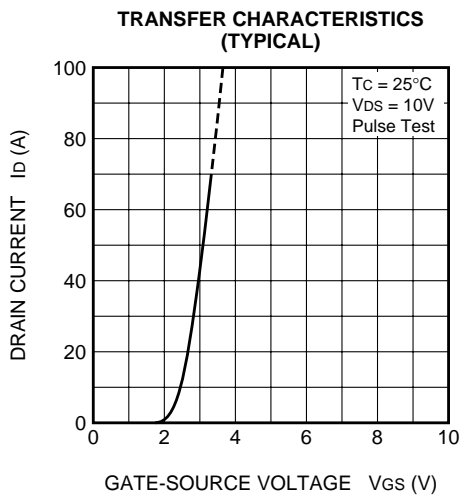
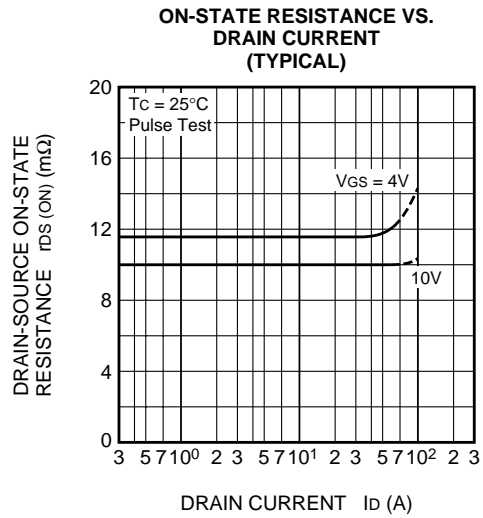
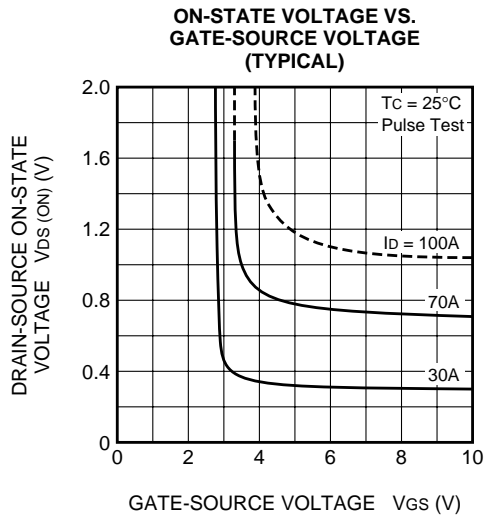


OUTPUT CHARACTERISTICS (TYPICAL)

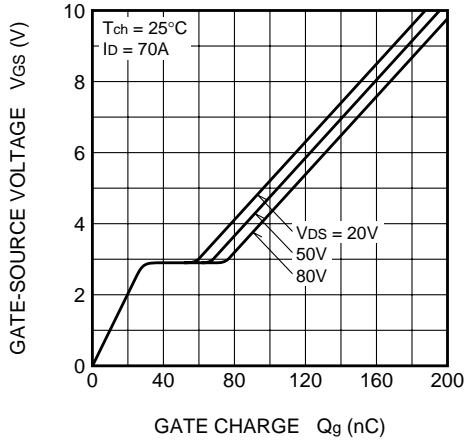


OUTPUT CHARACTERISTICS (TYPICAL)

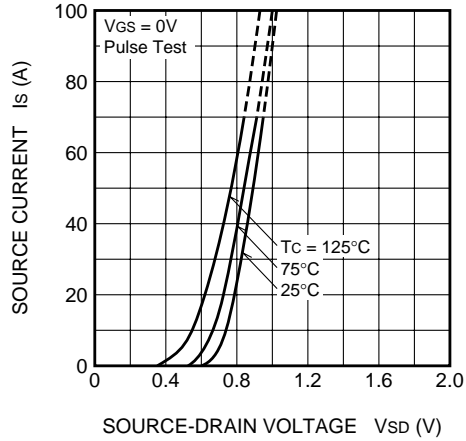




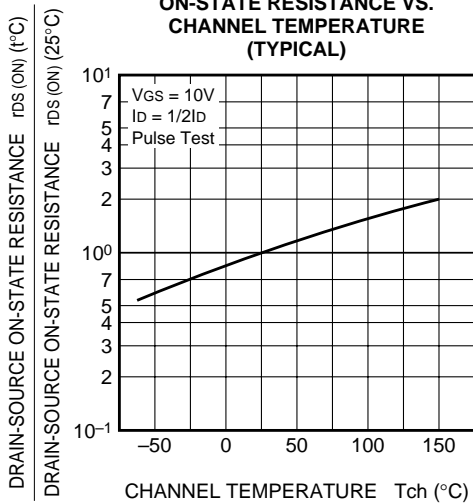
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



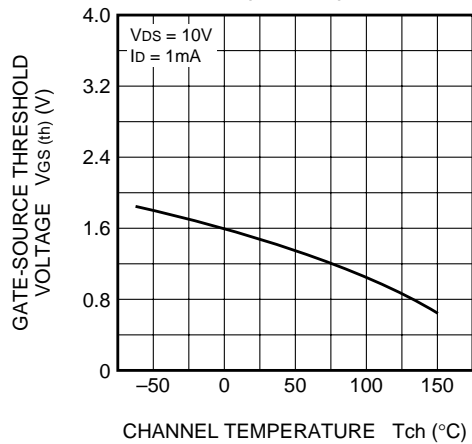
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



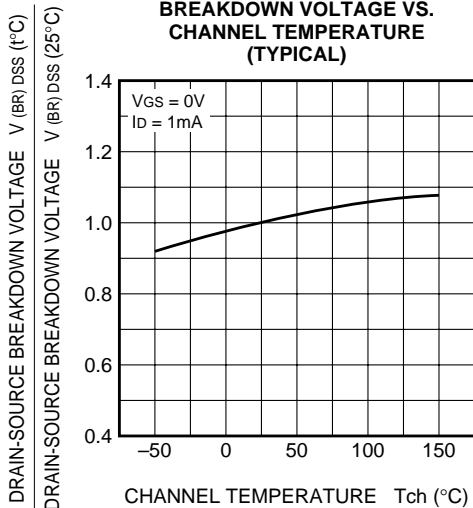
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

